

UNISONIC TECHNOLOGIES CO., LTD

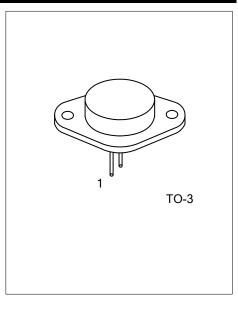
2N3772

SILICON NPN TRANSISTOR

SILICON NPN TRANSISTORS

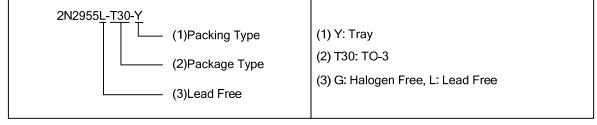
DESCRIPTION

The UTC **2N3772** is a silicon power transistor in TO-3 metal case. It is designed for linear amplifiers, series pass regulators, and inductive switching applications.



ORDERING INFORMATION

Ordering Number		Deelvere	Pin Assignment			Decking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2N3772L-T30-Y	2N3772G-T30-Y	TO-3	В	E	С	Tray	



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Collector-Emitter Voltage	V _{CEV}	80	V
Collector Current	lc	30	А
Collector Peak Current (Note 1)	I _{CM}	30	А
Base Current	Ι _Β	5	А
Base Peak Current (Note 1)	I _{BM}	15	А
Power Dissipation (T _A =25°C)	PD	150	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note 1. Pulse Test: P_W<=300µs, Duty Cycle<=2%

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

					r		
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Collector-Emitter Sustaining Voltage	V _{CEX(SUS)}	I _C =0.2A,V _{BE(OFF)} =1.5V,R _{BE} =100Ω	80			V	
Collector-Emitter Sustaining Voltage	V _{CER(SUS)}	I _C =0.2A, R _{BE} =100Ω	70			V	
Collector-Emitter Sustaining Voltage	V _{CEO(SUS)}	I _C =0.2A, I _B =0	60			V	
Collector Cut-off Current	I _{CEO}	V _{CE} =50V,I _B =0			10	mA	
Collector Cut-off Current	I _{CEX}	V _{CE} =100V, V _{BE(OFF)} =1.5V.			5	mA	
		V _{CE} =30V, V _{BE(OFF)} =1.5V, T _A =150℃			10		
Collector Cut-off Current	I _{CBO}	V _{CE} =50V, I _E =0			5	mA	
Emitter Cut-off Current	I _{EBO}	V _{BE} =7V, I _C =0			5	mA	
ON CHARACTERISTICS							
DC Current Cain (Nata)	h _{FE}	I _C =10A,V _{CE} =4V	15		60		
DC Current Gain (Note)		I _C =20A, V _{CE} =4V	5				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =10A, I _B =1.5A			1.4	V	
		I _C =20A, I _B =4A			4.0		
Base-Emitter On Voltage	V _{BE(ON)}	I _C =10A, V _{CE} =4V			2.2	V	
SECOND BREAKDOWN							
econd Breakdown Collector with Base		V _{CE} =60V, T=1.0s, Non-repetitive	2.5			А	
Forward Biased	IS/D		2.0			~	
DYNAMIC CHARACTERISTICS	r					-	
Current Gain-Bandwidth Product	f⊤	I _C =1A, V _{CE} =4V, f=50kHz	0.2			MHz	
Small-Signal Current Gain	h _{FE}	I _C =1A, V _{CE} =4V, f=1kHz	40				

Note: Pulse Test: P_W <=300 μ s, Duty Cycle<=2%



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

